



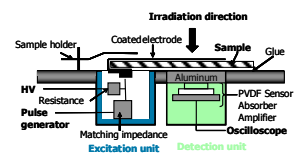
# BEHAVIOUR OF ELECTRON BEAM IRRADIATED POLYMERS: PEA MEASUREMENTS AND SIMULATIONS

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**Synopsis:** Under specific space environment conditions, polymeric materials used as cover parts of satellites can store charges, leading to electrostatic discharges. In order to understand the behavior of dielectrics under electronic irradiation, the spatial environment is reproduced at lab-scale. The space charge distribution is studied by Pulse Electro Acoustic (PEA) system that has been implemented to reproduce two configurations (short-circuit and open). To complete these studies simulation models have been developed. Experimental and simulation results obtained on Low Density Poly Ethylene (LDPE) irradiated films are presented and discussed here.

## EXPERIMENTAL SET-UPS

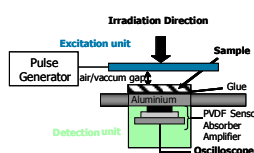
### SHORT-CIRCUIT PEA



- + Excitation and detection units on the same side
- + Coated electrode on the front to apply the pulse probe voltage
- + Both surfaces grounded between measurements
- + Measurements at any time during irradiation and relaxation

→ Configuration representative of dielectrics located on sun lighted satellite side where the photoemission is effective

### OPEN PEA



- + Electrode positioned at 1 mm above the sample
- + Extraction of charges only at the ground electrode
- + Measurements performed between two periods of irradiation, and anytime during relaxation

→ Configuration representative of dielectrics covering the satellite and not exposed to the sun

## SIMULATIONS

### MODEL DESCRIPTION

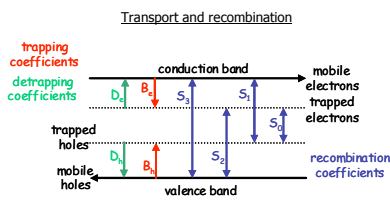


Figure 1: Schematic representation of the conduction mechanisms used in the simulation. The values and definition of the parameters are given in the Table.

### Equations

$$j(x,t) = n(x,t) \cdot E(x,t) \quad \text{transport} \quad \frac{\partial E(x,t)}{\partial x} = \frac{\rho(x,t)}{\epsilon} \quad \text{Poisson}$$

$$\frac{\partial n(x,t)}{\partial t} + \frac{\partial j(x,t)}{\partial x} = s \quad \text{continuity}$$

Example of source term for mobile electrons

$$s_e(x,t) = -\frac{\partial J_0(x,t)}{\partial x} + G(x) \cdot B_e \cdot n_e(x,t) \left(1 - \frac{n_e}{n_{tot}}\right) + D_e \cdot n_{ei} - S_1 \cdot n_e \cdot n_{tr} - S_2 \cdot n_e \cdot n_{tr}$$

Electron beam current density

Refers to electron/hole pairs generation due to the electron beam:

$$G(x) = G_0 \cdot D(x)$$

### PARAMETERS USED FOR ALL SIMULATIONS

Symbol	Value	units
<b>mobility</b>	$\mu_e$	$1 \cdot 10^{-14} \text{ m}^2 \cdot \text{V}^{-1} \cdot \text{s}^{-1}$
	$\mu_h$	$2 \cdot 10^{-13}$
<b>Deep trapping coefficient</b>	$B_e$	$1 \cdot 10^{-1}$
	$B_h$	$2 \cdot 10^{-1}$
<b>injection barrier height</b>	$w_e$	1.27 eV
	$w_h$	1.16 eV
<b>Deep trap densities</b>	$N_{tot}$	100 $\text{C} \cdot \text{m}^{-3}$
	$N_{dtr}$	100 $\text{C} \cdot \text{m}^{-3}$
<b>Recombination coefficients</b>	$S_1, S_2, S_3$	0 $\text{m}^3 \cdot \text{C}^{-1} \cdot \text{s}^{-1}$
<b>Detrapping barrier height</b>	$w_{tr}$	0.96 eV
	$w_{tr}$	0.99 eV
<b>Electron/hole pairs generation coefficient</b>	$G_0$	$5 \cdot 10^{-2} \text{ C} \cdot \text{m}^{-3} \cdot \text{s}^{-1}$

## COMPARISONS BETWEEN EXPERIMENTAL AND SIMULATED SPACE CHARGES PROFILES

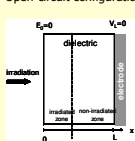
### EXPERIMENTAL CONDITIONS :

- LDPE sample of thickness 500  $\mu\text{m}$
- Electron beam energy: 200 keV
- Beam current density: 50  $\text{pA} \cdot \text{cm}^{-2}$
- irradiation: 36 min
- relaxation: 1 day

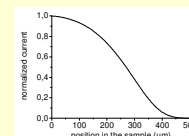
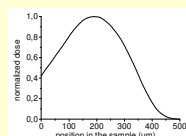
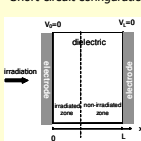
### IRRADIATION DOSE AND CURRENT PROFILES :

Dose  $D(x)$  and current  $J_0(x)$  calculated with GEANT 4 software, used for the simulation of deposited electrons and electron/hole pairs generation due to the electron beam

### Open-circuit configuration



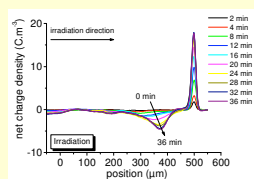
### Short-circuit configuration



### OPEN CIRCUIT CONFIGURATION

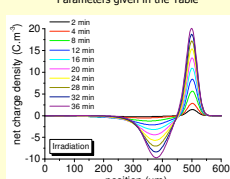
#### IRRADIATION

#### Experiment



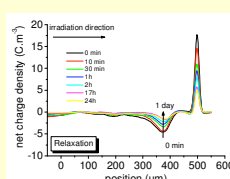
#### Simulation

Parameters given in the Table



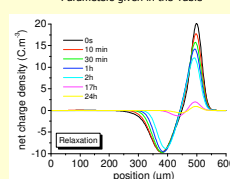
#### RELAXATION

#### Experiment



#### Simulation

Parameters given in the Table



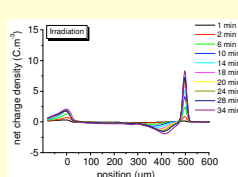
Simulated profiles consistent with experimental ones during irradiation

The dynamic of charges is too fast in the simulation compared with the experiment.

### SHORT CIRCUIT CONFIGURATION

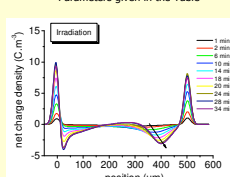
#### IRRADIATION

#### Experiment



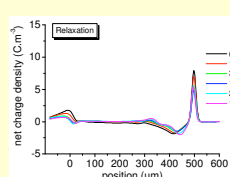
#### Simulation

Parameters given in the Table



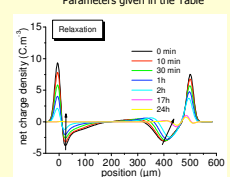
#### RELAXATION

#### Experiment



#### Simulation

Parameters given in the Table



Simulated profiles show the main negative peak at ~400  $\mu\text{m}$  as in the experiments. It also shows a second negative peak next to the irradiation face.

Simulated profiles show a displacement of the negative peak at 400  $\mu\text{m}$ , and the relaxation of the majority of the charges after one day.

## CONCLUSION

**OPEN CIRCUIT Configuration:** the model is able to reproduce the dynamic of charge during electron beam irradiation and during relaxation

**SHORT CIRCUIT Configuration:** Some experimental features are reproduced by the model (peak at ~400  $\mu\text{m}$ ).